

N-channel 600 V, 1.3 Ω typ., 3.5 A MDmesh™ M2 Power MOSFET in a TO-220FP package

Datasheet - production data

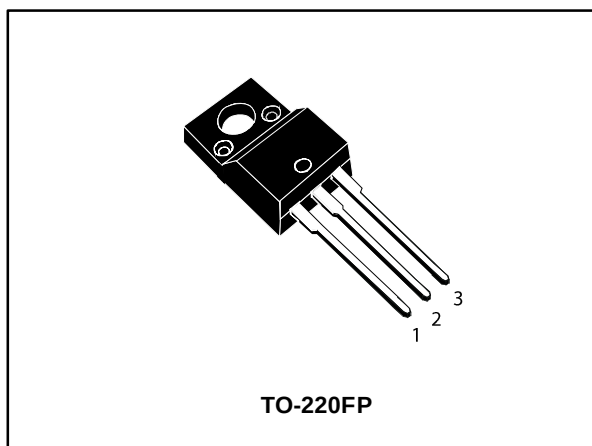
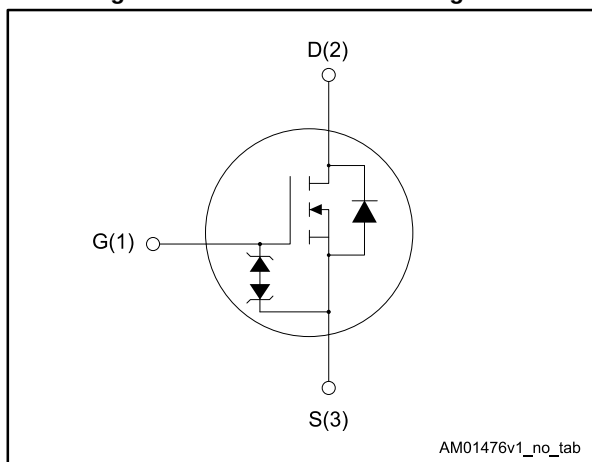


Figure 1: Internal schematic diagram



Features

Order code	$V_{DS}@ T_{Jmax}$	$R_{DS(on)}$ max.	I_D
STF5N60M2	650 V	1.4 Ω	3.5 A

- Extremely low gate charge
- Excellent output capacitance (C_{OSS}) profile
- 100% avalanche tested
- Zener-protected

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using MDmesh™ M2 technology. Thanks to its strip layout and an improved vertical structure, the device exhibits low on-resistance and optimized switching characteristics, rendering it suitable for the most demanding high efficiency converters.

Table 1: Device summary

Order code	Marking	Package	Packing
STF5N60M2	5N60M2	TO-220FP	Tube

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1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	± 25	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	3.5	A
	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	2.2	
$I_{DM}^{(2)}$	Drain current (pulsed)	14	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	20	W
V_{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink ($t = 1\text{ s}$; $T_C = 25\text{ }^\circ\text{C}$)	2500	V
$dv/dt^{(3)}$	Peak diode recovery voltage slope	15	V/ns
$dv/dt^{(4)}$	MOSFET dv/dt ruggedness	50	
T_{stg}	Storage temperature range	-55 to 150	$^\circ\text{C}$
T_j	Operating junction temperature range		

Notes:

(1) Limited by package.

(2) Pulse width limited by safe operating area.

(3) $I_{SD} \leq 3.5\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$; $V_{DS\text{ peak}} < V_{(BR)DSS}$, $V_{DD} = 400\text{ V}$.(4) $V_{DS} \leq 480\text{ V}$.

Table 3: Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max.	6.25	$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient max.	62.5	$^\circ\text{C}/\text{W}$

Table 4: Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not repetitive (pulse width limited by T_{jmax})	0.5	A
E_{AS}	Single pulse avalanche energy (starting $T_j = 25\text{ }^\circ\text{C}$, $I_D = I_{AR}$; $V_{DD} = 50\text{ V}$)	80	mJ

2 Electrical characteristics

($T_{\text{case}} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Table 5: On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(\text{BR})\text{DSS}}$	Drain-source breakdown voltage	$V_{\text{GS}} = 0\text{ V}$, $I_{\text{D}} = 1\text{ mA}$	600			V
I_{DSS}	Zero gate voltage drain current	$V_{\text{GS}} = 0\text{ V}$, $V_{\text{DS}} = 600\text{ V}$			1	μA
		$V_{\text{GS}} = 0\text{ V}$, $V_{\text{DS}} = 600\text{ V}$, $T_{\text{C}} = 125\text{ }^{\circ}\text{C}$ ⁽¹⁾			100	
I_{GSS}	Gate-body leakage current	$V_{\text{DS}} = 0\text{ V}$, $V_{\text{GS}} = \pm 25\text{ V}$			± 10	μA
$V_{\text{GS(th)}}$	Gate threshold voltage	$V_{\text{DS}} = V_{\text{GS}}$, $I_{\text{D}} = 250\text{ }\mu\text{A}$	2	3	4	V
$R_{\text{DS(on)}}$	Static drain-source on-resistance	$V_{\text{GS}} = 10\text{ V}$, $I_{\text{D}} = 1.7\text{ A}$		1.3	1.4	Ω

Notes:

⁽¹⁾ Defined by design, not subject to production test.

Table 6: Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{\text{DS}} = 100\text{ V}$, $f = 1\text{ MHz}$, $V_{\text{GS}} = 0\text{ V}$	-	211	-	pF
C_{oss}	Output capacitance		-	13	-	
C_{rss}	Reverse transfer capacitance		-	0.75	-	
$C_{\text{oss eq.}}^{(1)}$	Equivalent output capacitance	$V_{\text{DS}} = 0\text{ to }480\text{ V}$, $V_{\text{GS}} = 0\text{ V}$	-	19.5	-	pF
R_{G}	Intrinsic gate resistance	$f = 1\text{ MHz}$ open drain	-	6.2	-	Ω
Q_{g}	Total gate charge	$V_{\text{DD}} = 480\text{ V}$, $I_{\text{D}} = 3.5\text{ A}$, $V_{\text{GS}} = 10\text{ V}$ (see Figure 15: "Test circuit for gate charge behavior")	-	8	-	nC
Q_{gs}	Gate-source charge		-	1.6	-	
Q_{gd}	Gate-drain charge		-	4.4	-	

Notes:

⁽¹⁾ $C_{\text{oss eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS} .

Table 7: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{\text{d(on)}}$	Turn-on delay time	$V_{\text{DD}} = 300\text{ V}$, $I_{\text{D}} = 1.7\text{ A}$ $R_{\text{G}} = 4.7\text{ }\Omega$, $V_{\text{GS}} = 10\text{ V}$ (see Figure 14: "Test circuit for resistive load switching times" and Figure 19: "Switching time waveform")	-	12	-	ns
t_{r}	Rise time		-	3	-	
$t_{\text{d(off)}}$	Turn-off delay time		-	70	-	
t_{f}	Fall time		-	15	-	

Table 8: Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		3.5	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		14	A
$V_{SD}^{(2)}$	Forward on voltage	$V_{GS} = 0\text{ V}$, $I_{SD} = 3.5\text{ A}$	-		1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 3.5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 60\text{ V}$ (see Figure 16: "Test circuit for inductive load switching and diode recovery times")	-	220		ns
Q_{rr}	Reverse recovery charge		-	1.05		μC
I_{RRM}	Reverse recovery current		-	9.5		A
t_{rr}	Reverse recovery time	$I_{SD} = 3.5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 60\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ (see Figure 16: "Test circuit for inductive load switching and diode recovery times")	-	314		ns
Q_{rr}	Reverse recovery charge		-	1.5		μC
I_{RRM}	Reverse recovery current		-	9.5		A

Notes:

⁽¹⁾ Pulse width is limited by safe operating area.

⁽²⁾ Pulse test: pulse duration = 300 μs , duty cycle 1.5 %.

2.1 Electrical characteristics (curves)

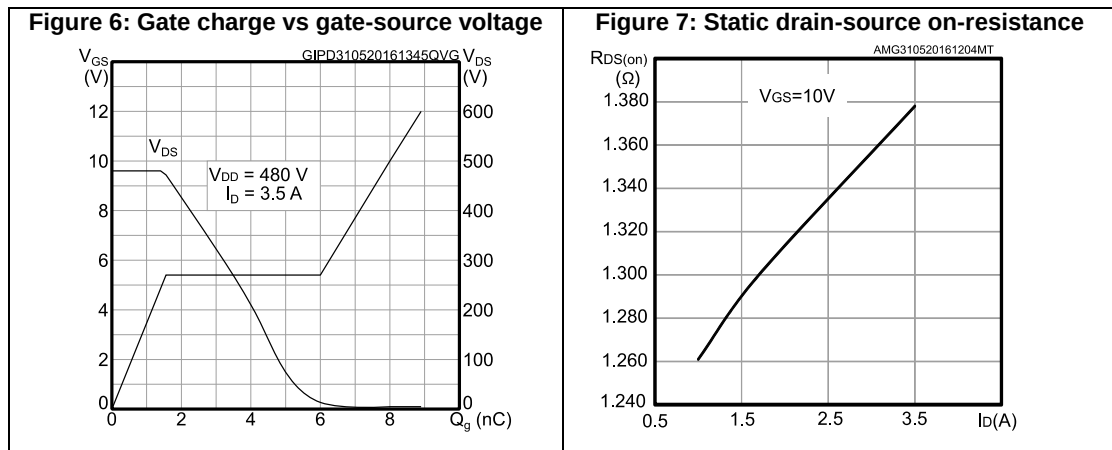
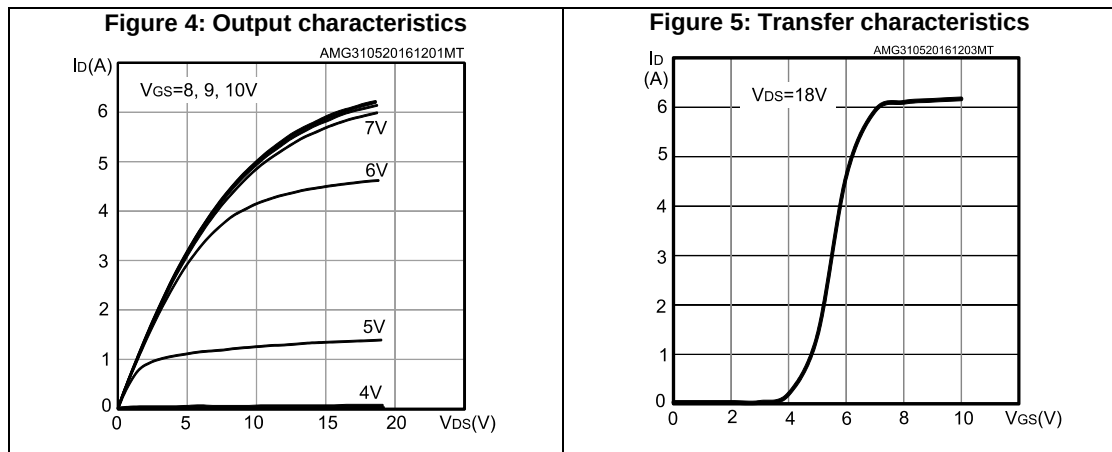
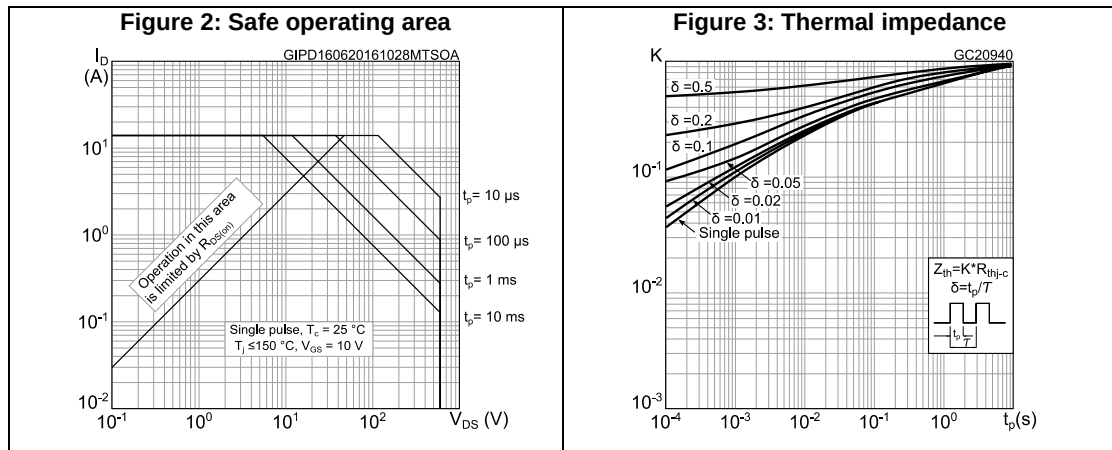


Figure 8: Capacitance variations

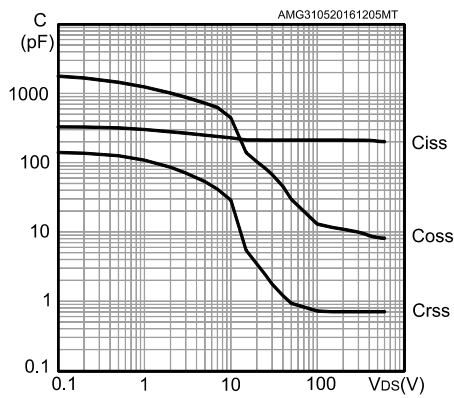


Figure 9: Output capacitance stored energy

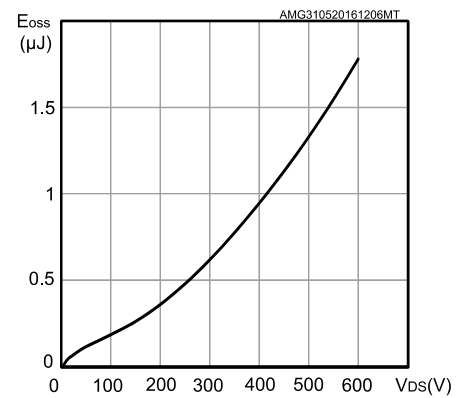


Figure 10: Normalized gate threshold voltage vs temperature

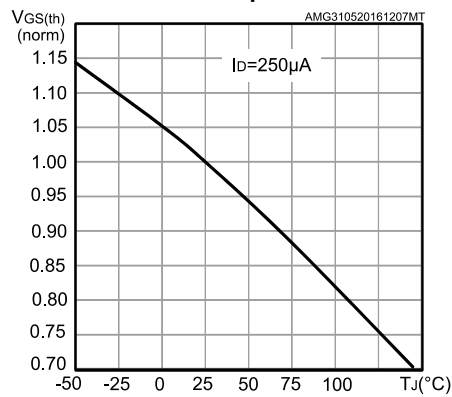


Figure 11: Normalized on-resistance vs temperature

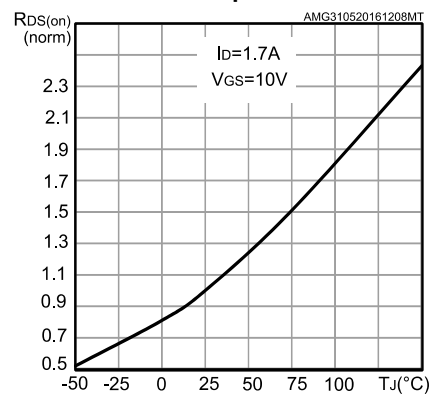


Figure 12: Normalized V(BR)DSS vs temperature

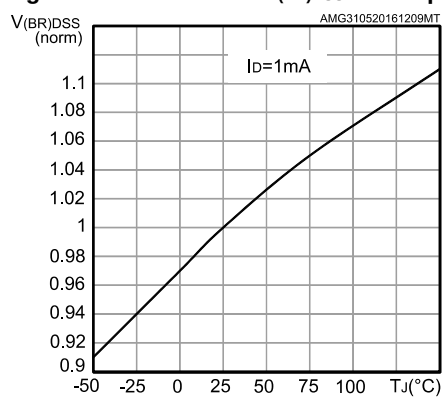
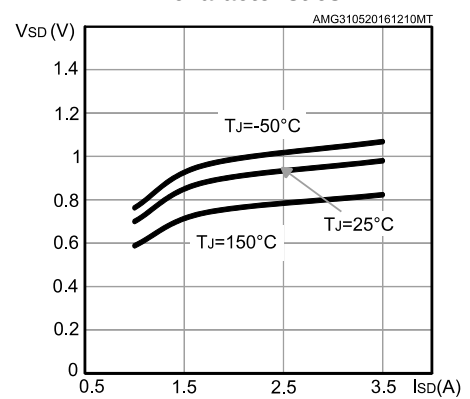
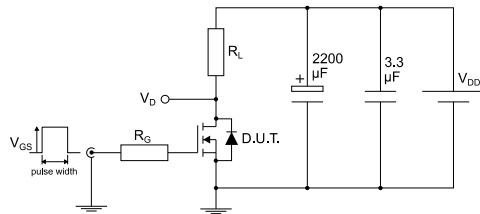


Figure 13: Source-drain diode forward characteristics



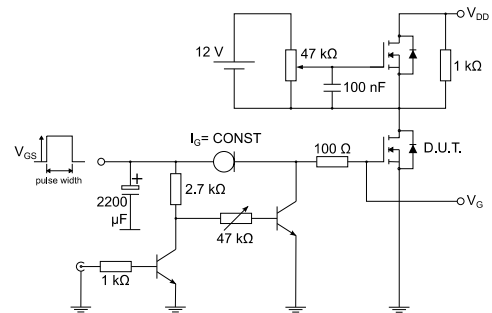
3 Test circuits

Figure 14: Test circuit for resistive load switching times



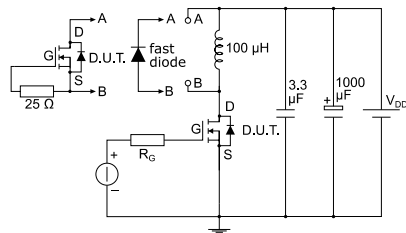
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Figure 15: Test circuit for gate charge behavior



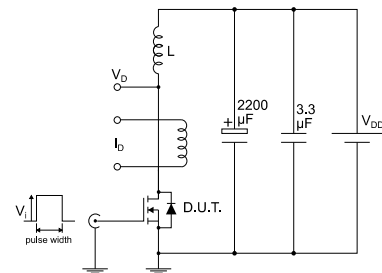
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Figure 16: Test circuit for inductive load switching and diode recovery times



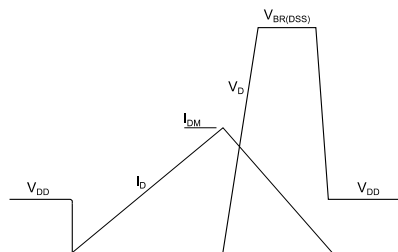
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Figure 17: Unclamped inductive load test circuit



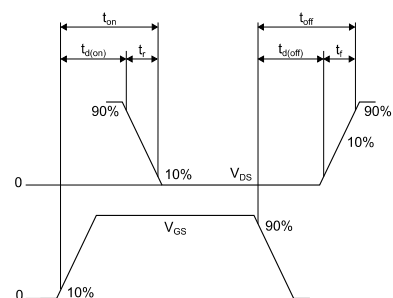
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Figure 18: Unclamped inductive waveform



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Figure 19: Switching time waveform



AM01473v1

4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: **www.st.com**. ECOPACK® is an ST trademark.

4.1 TO-220FP package information

Figure 20: TO-220FP package outline

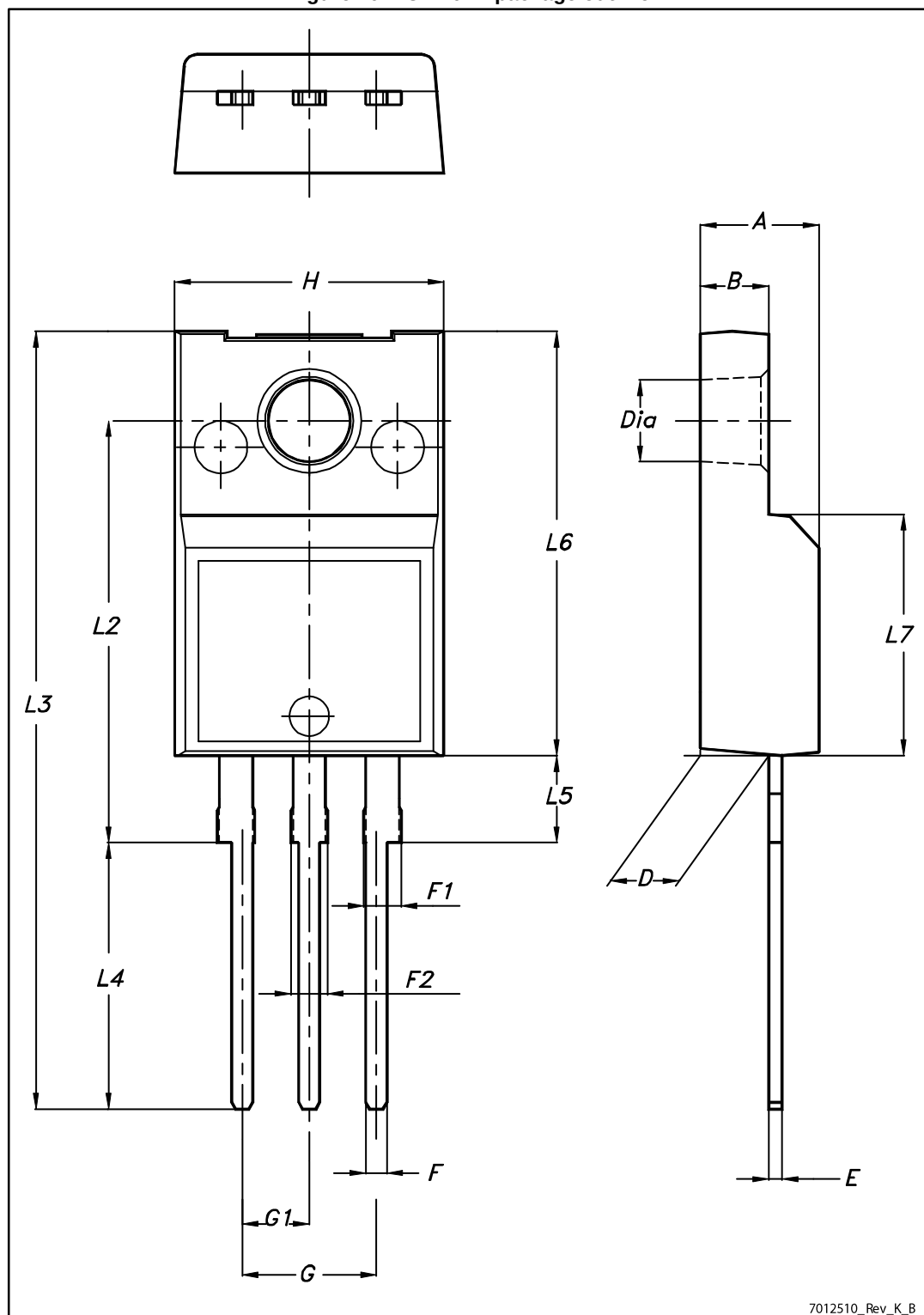


Table 9: TO-220FP package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

5 Revision history

Table 10: Document revision history

Date	Revision	Changes
30-Sep-2013	1	First release.
15-Jun-2016	2	Updated title, features and description in cover page. Updated Section 1: "Electrical ratings" and Section 2: "Electrical characteristics" . Added Section 2.1: "Electrical characteristics (curves)" . Minor text changes.

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